FORM PTO-1449 (Rev. 7-80) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. NREL 99-50	SERIAL NO. 09/841,691
LIST OF PRIOR ART CITED BY APPLICANT (Use several sheets if necessary)	APPLICANT(S) Mascarenhas, Angelo	
	FILING DATE April 24, 2001	GROUP Not Yet Accorded

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AA	6,002,202	December 14, 1999	Meyer *et al.*	313	420	
AB	5,986,288	November 16, 1999	Hasegawa	257	94	
AC	5,963,571	October 5, 1999	Wingreen	372	45	
AD	5,895,225	April 20, 1999	Kidoguchi *et al.*	438	47	
AE	5,776,793	July 7, 1998	Lee *et al.*	438	35	
AF	5,728,231	March 17, 1998	Negami *et al.*	148	33	
AG	5,453,404	September 26, 1995	Leedy	437	203	
AH	5,387,544	February 7, 1995	Hayafuji	437	151	
AI	5,344,791	September 6, 1994	Huang	437	126	
AJ	5,231,298	July 27, 1993	Daly	257	191	
AK	5,158,896	October 27, 1992	Burroughes *et al.*	437	5	
AL	5,116,455	May 26, 1992	Daly	156	605	
AM	5,028,561	July 2, 1991	Kamath *et al.*	437	105	
AN	4,939,103	July 3, 1990	Szolgyemy	437	151	
AO	4,591,654	May 27, 1986	Yamaguchi *et al.*	136	252	
AP	4,400,221	August 23, 1983	Rahilly	148	1.5	
AQ	4,284,962	August 18, 1981	Esterowitz *et al.*	331	94.5 F	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

AR	Oe, K. and Okamoto, H., "New Semiconductor Alloy $AgAs_{1-x}Bi_x$ Grown by Metal Organic Vapor Phase Expitaxy",
	Japanese Journal of Applied Physics, Vol. 37, pp. L1283 - L1285, November 1998.
AS	Yamamoto, T. and Katayama-Yoshida, H., "Solution Using a Codoping Method to *Unipolarity* for the Fabrication of
	p-Type ZnO", *Japanese Journal of Applied Physics, Vol 38, pt. 2, no. 2B, pp. L166 - L169, Feb. 1999*

	AT	Ploog, K.H. and Brandt, O., "Doping of group III nitrides", *Journal of Vacuum Society Technology A*, Vol. 16, No. 3,
		pg. 1609, August 1998.
	AU	Yamamoto, T. and Katayama-Yoshida, H. "Role of Clor I Codoping in Li-Doping Enhancement in ZnSe",
		Japanese Journal of Applied Physics, Pt. 2, No. 8A, pp. L910 - L912, August 1998.
	AV	Brandt, O.; Yang, H.; Kostial, H.; and Ploog, K.H., "High *p*-type condicutivity in cubic GaN/GaAs(113)*A* by using Be
		as the acceptor and O as the codopant", *Applied Physics Letters*, Vol. 69, No. 18, pp. 2707 - 2709, October 1996.
	AW	Pankove, J.I.; Torvid, J.T.; Qui, C.-H.; Grzegory, I.; Porowski, S.; Qui, C.-H.; Grzegory, I.; Porowski, S.; Quigley, P.;
		Martin, B., "Molecular Doping of Gallium Nitride", *Applied Physics Letters*, Vol. 74, No. 3, pp. 416 - 418, Jan. 1999.
	AX	White, C.W.; Budai, J.D.; Zhu, J.G; and Withrow, S.P., "Ion-beam systhesis and stability of GaAs Nanocrystals in
		silicon", *Applied Physics Letters*, Vol. 68, No. 17, pp. 2389 - 2391, April 1996.
	AY	Withrow, S.P.; Holland, O.W.; Pennycook, S.J.; Pankeve, J.; and Mascarenhas, A., "Beam-Solid Interactions: Physical
		Phenomena", *Materials Research Society Symposium Proceedings*, Vol. 157, pp. 143 - 148, (1990).
	AZ	Kuznetsov, V.V.; Pikhtin, A.N.; Razbegaev, V.N.; and Sorokin, V.S., "High-temperature luminescence of GaP:Bi:N",
		Sov. Phys. Semicond., 14(4), pp. 417 - 419, April 1980.
	BA	Trumbore, M.; Gershenzon, M.; and Thomas, D.G., "Luminescence due to the Isoelectronic Substitution of Bismuth for
		Phosphorus in Gallium Phosphide", *Applied Physics Letters*, Vol. 9, No. 1, pp. 4 - 6, July 1966.
EXAMINER		2/03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not